

**MAGNETIC MEMORY WHICH DETECTS CHANGES BETWEEN
FIRST AND SECOND RESISTIVE STATES OF A
MEMORY CELL**

5

Abstract of the Disclosure

A magnetic memory which detects changes between resistive states of a memory cell is disclosed. In one embodiment the magnetic memory includes a memory cell which has first and second resistive states. First and second write conductors are configured to conduct first and second currents to change the
10 memory cell between the first and the second resistive states. The first and the second write conductors are routed in first and second directions and intersect the memory cell. First and second sense conductors are configured to conduct a sense current through the memory cell. A sense circuit coupled to the second sense conductor is configured to detect the change between the first and the
15 second resistive states.